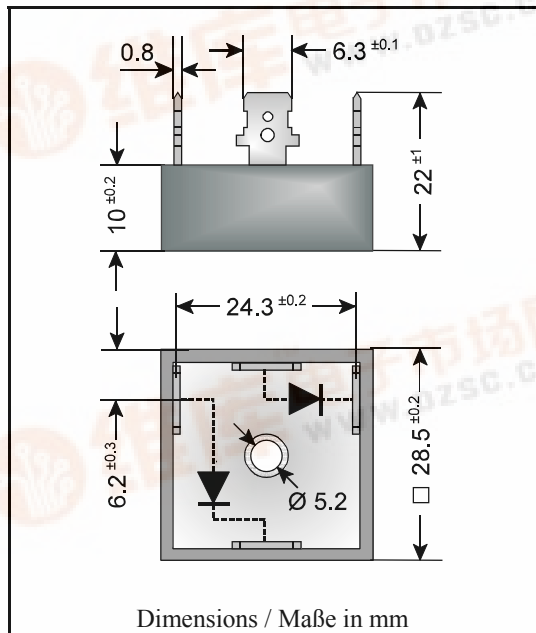


Silicon-Twin Rectifiers

Silizium-Doppeldioden



Nominal current 60 A
Nennstrom

Alternating input voltage 60...800 V
Eingangswechselspannung

Plastic case with alu-bottom
Kunststoffgehäuse mit Alu-Boden

Dimensions 28.5 x 28.5 x 10 [mm]
Abmessungen

Weight approx. 23 g
Gewicht ca.

Compound has classification UL94V-0
Vergußmasse UL94V-0 klassifiziert

Standard packaging: bulk see page 22
Standard Lieferform: lose im Karton s. Seite 22



Recognized Product – Underwriters Laboratories Inc.® File E175067
Anerkanntes Produkt – Underwriters Laboratories Inc.® Nr. E175067

Maximum ratings

Grenzwerte

Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] ¹⁾	Surge peak reverse voltage Stoßspitzensperrspannung V_{RRM} [V] ¹⁾
D60 VC20	200	200
D60 VC40	400	400
D60 VC60	600	600
D60 VC80	800	800
D60 VC100	1000	1000
D60 VC120	1200	1200

Repetitive peak forward current $f > 15$ Hz I_{FRM} 120 A ²⁾
Periodischer Spitzenstrom

Peak forward surge current, 50 Hz half sine-wave $T_A = 25^\circ\text{C}$ I_{FSM} 450 A
Stoßstrom für eine 50 Hz Sinus-Halbwellen

Rating for fusing – Grenzlastintegral, $t < 10$ ms $T_A = 25^\circ\text{C}$ i^2t 1000 A²s

Isolation voltage – Isolationsspannung $t = 1$ min V_{ISO} > 2000 V

Operating junction temperature – Sperrschichttemperatur T_j $-50...+150^\circ\text{C}$
Storage temperature – Lagerungstemperatur T_s $-50...+150^\circ\text{C}$

¹⁾ Valid per diode – Gültig pro Diode

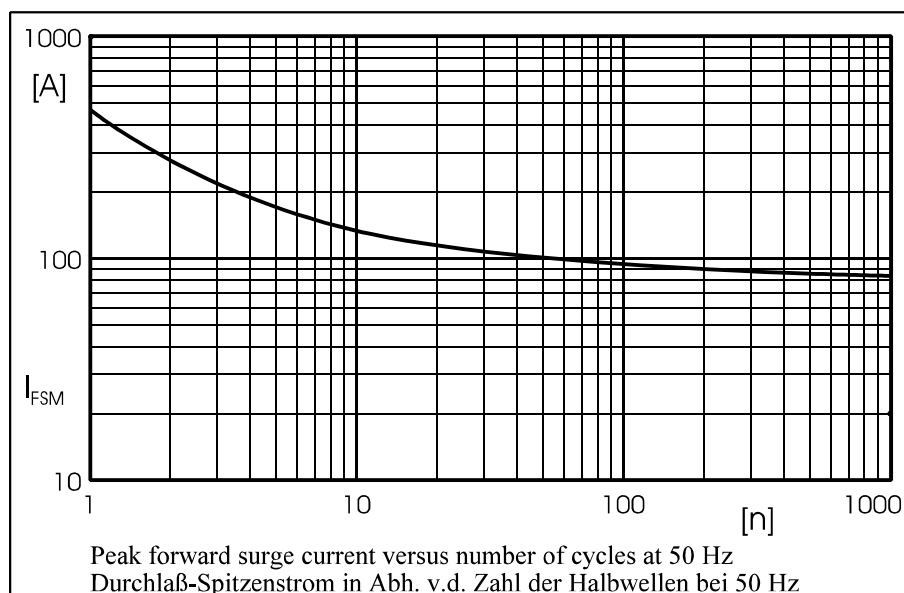
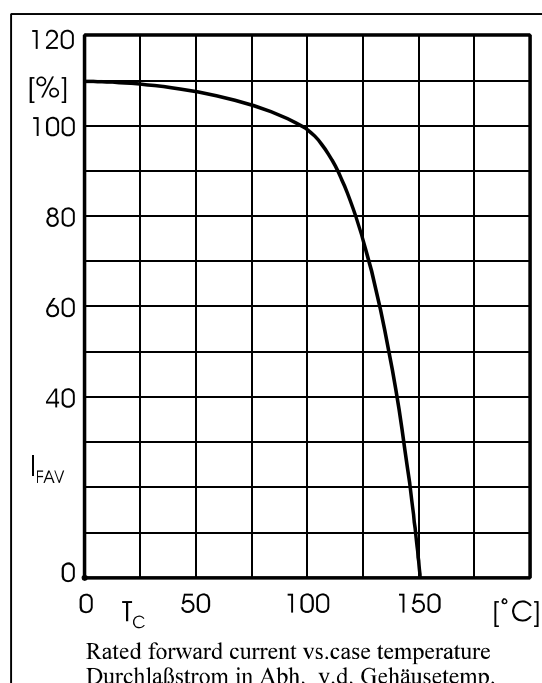
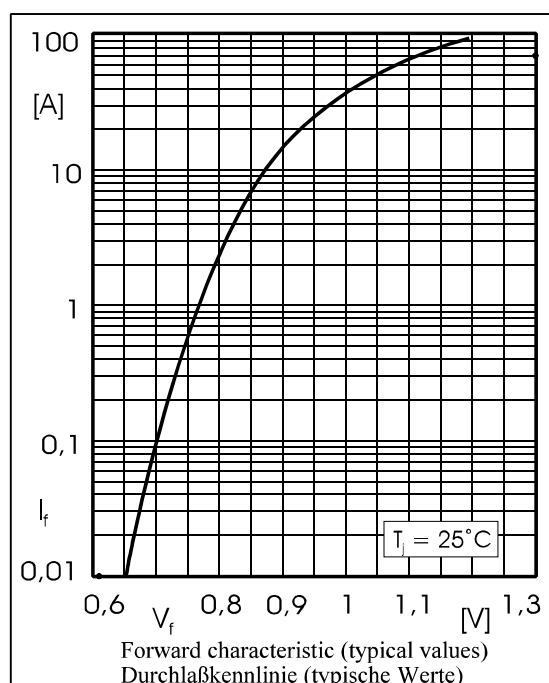
²⁾ Max. case temperature $T_C = 100^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 100^\circ\text{C}$



Characteristics

Kennwerte

Forward voltage – Durchlaßspannung	$T_j = 25^\circ\text{C}$	$I_F = 60\text{ A}$	V_F	$< 1.1\text{ V}^1)$
Leakage current – Sperrstrom	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	I_R	$< 100\text{ }\mu\text{A}$
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			R_{thC}	$< 0.6\text{ K/W}$
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		$18 \pm 10\%\text{ lb.in.}$ $2 \pm 10\%\text{ Nm}$



¹⁾ Valid per diode – Gültig pro Diode